

CoolGaN™ G5

CoolGaN™ Transistor 700 V G5

Infineon's CoolGaN™ is a highly efficient gallium nitride (GaN) transistor designed for power conversion at 700 V. It enables higher power density, supports reduced system BOM cost, and facilitates miniaturized form factors. Produced using 200 mm (8 inch) wafer technology and fully automated production lines, it features narrow production tolerances and the highest product quality.

Features

- Enhancement mode transistor
- Ultra-fast switching
- No reverse-recovery charge
- Capable of reverse conduction
- Low gate and output charge
- Superior commutation ruggedness
- 2 kV HBM ESD standards

Benefits

- Normally OFF transistor technology ensures safe operation
- Enables rapid and precise power delivery control
- Improves system efficiency and reliability
- Ensures robust performance under challenging conditions

These features collectively make CoolGaN™ a game-changer in the realm of power conversion, offering a compelling combination of efficiency, compactness, and reliability.

Potential applications

Consumer QR applications with zero current turn on like charger, adapter, TV power, home appliance
(not recommended for hard switching topologies)

Product validation

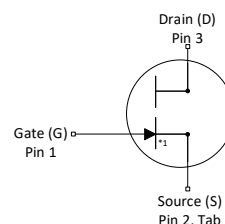
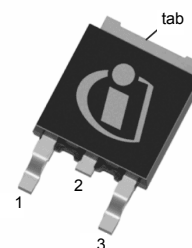
Qualified for applications according to the test conditions in the relevant tests of JEDEC JESD22 and J-STD-020.

Table 1 Key performance parameters

Parameter	Value	Unit
$V_{DS,max}$	700	V
$V_{DS,trans-max}$	900	V
$R_{DS(on),max}$	240	mΩ
$Q_{g,typ}$	1.3	nC
$I_{D,pulse}$	16	A
$Q_{oss} @ 400 V$	9.6	nC
Q_{rr}	0	nC

Part number	Package	Marking	Related links
IGD70R200D2S	PG-TO252-3	70R200D2	see Appendix A

PG-TO252-3



*1: Internal gate diode

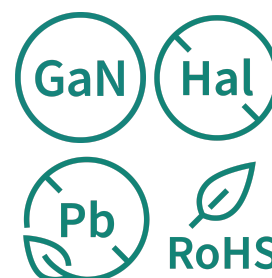




Table of contents

Description 1

Maximum ratings 3

Thermal characteristics 5

Electrical characteristics 6

Electrical characteristics diagrams 8

Test circuits 13

Package outlines 14

Appendix A 15

Revision history 16

Trademarks 17

Disclaimer 17

1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified. Stresses beyond max ratings may cause permanent damage to the device. For optimum lifetime and reliability, Infineon recommends operating conditions that do not continuously exceed 80% of the maximum ratings stated (unless otherwise explicitly stated). For further information, contact your local Infineon sales office.

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain source voltage, continuous	$V_{DS,max}$	-	-	700	V	$V_{GS} = 0\text{ V}$; derating recommendation according JEDEC JEP198
Leakage current at drain source transient voltage	$I_{DS,trans}$	-	-	3.3	mA	$V_{GS} = 0\text{ V}$; $V_{DS,trans} = 900\text{ V}$
Drain source voltage transient	$V_{DS,trans}$	-	-	900	V	<1% duty cycle; <1 μs ; 1 million pulses
Drain source voltage, pulsed	$V_{DS,pulsed}$	-	-	750	V	$T_j = 25^\circ\text{C}$; $V_{GS} \leq 0\text{ V}$; cumulated stress time $\leq 10\text{ h}$
						$T_j = 125^\circ\text{C}$; $V_{GS} \leq 0\text{ V}$; cumulated stress time $\leq 1\text{ h}$
Switching surge voltage, pulsed	$V_{DS,surge}$	-	-	750	V	DC bus voltage = 700 V; turn off $V_{DS,pulse} = 750\text{ V}$; turn on $I_{D,pulse} = 7.3\text{ A}$; $f \leq 100\text{ kHz}$; $T_j = 105^\circ\text{C}$; $t \leq 100\text{ s}$ (10 million pulses)
Continuous current, drain source ¹⁾	I_D	-	-	7.3	A	$T_C = 25^\circ\text{C}$; $T_j = T_{j,max}$
Pulsed current, drain source	$I_{D,pulse}$	-16	-	16	A	$T_j = 25^\circ\text{C}$; $I_G = 7.1\text{ mA}$; See Diagram 3, 5
		-9.7		9.7		$T_j = 125^\circ\text{C}$; $I_G = 7.1\text{ mA}$; See Diagram 4, 6
Gate current, continuous ²⁾	$I_{G,avg}$	-	-	5.3	mA	$T_j = -55^\circ\text{C}$ to $T_j = 150^\circ\text{C}$; See Table 9
Gate current, pulsed ²⁾	$I_{G,pulsed}$	-0.53	-	0.53	A	$T_j = -55^\circ\text{C}$ to $T_j = 150^\circ\text{C}$; $t_{pulse} = 50\text{ ns}$; $f = 100\text{ kHz}$; See Table 9
Gate source voltage, continuous ²⁾	V_{GS}	-10	-	-	V	$T_j = -55^\circ\text{C}$ to $T_j = 150^\circ\text{C}$; See Diagram 12
Gate source voltage, pulsed ²⁾	$V_{GS,pulse}$	-25	-	-	V	$T_j = -55^\circ\text{C}$ to $T_j = 150^\circ\text{C}$; $t_{pulse} = 50\text{ ns}$; $f = 100\text{ kHz}$; open drain
Power dissipation	P_{tot}	-	-	21	W	$T_C = 25^\circ\text{C}$
Operating junction temperature ³⁾	T_j	-40	-	150	$^\circ\text{C}$	-
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	Max shelf life depends on storage conditions
Drain-source voltage slew-rate	dv/dt	-	-	200	V/ns	-

- 1) Limited by $T_{j,max}$. Maximum duty cycle $D = 0.75$
- 2) We recommend using an advanced driving technique to optimize the device performance. Please see gate drive application note for more details.
- 3) For optimum lifetime and reliability, Infineon recommends average T_j operating temperature below 100°C. For further information, contact your local Infineon sales office.

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	6.0	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	150	°C/W	Device on PCB, minimum footprint
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	-	75	°C/W	Device on 40 mm*40 mm*1.5 mm epoxy PCB FR4 with 6 cm ² (one layer, 70 µm thickness) copper area for tab (source) connection and cooling. PCB is vertical without air stream cooling.
Soldering temperature	T_{sold}	-	-	260	°C	MSL3, wave & reflow soldering allowed

3 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless specified otherwise

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate threshold voltage	$V_{GS(th)}$	0.9	1.2	1.6	V	$I_{DS}=0.71\text{ mA}$; $V_{DS}=10\text{ V}$; $T_j=25^\circ\text{C}$
		-	1	-		$I_{DS}=0.71\text{ mA}$; $V_{DS}=10\text{ V}$; $T_j=150^\circ\text{C}$
Gate-Source reverse clamping voltage	$V_{GS, clamp}$	-	-	-8	V	$I_{GS}=-1\text{ mA}$
Drain-Source leakage current	I_{DSS}	-	1.2	120	μA	$V_{DS}=700\text{ V}$; $V_{GS}=0\text{ V}$; $T_j=25^\circ\text{C}$
			24	-		$V_{DS}=700\text{ V}$; $V_{GS}=0\text{ V}$; $T_j=150^\circ\text{C}$
Drain-Source on-state resistance	$R_{DS(on)}$	-	0.200	0.240	Ω	$I_G=7.1\text{ mA}$; $I_D=2.1\text{ A}$; $T_j=25^\circ\text{C}$
			0.430	-		$I_G=7.1\text{ mA}$; $I_D=2.1\text{ A}$; $T_j=150^\circ\text{C}$
Gate resistance	$R_{G,int}$	-	0.98	-	Ω	LCR impedance measurement; $f=f_{res}$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	91	-	pF	$V_{GS}=0\text{ V}$; $V_{DS}=400\text{ V}$; $f=1\text{ MHz}$
Output capacitance	C_{oss}		15			
Reverse transfer capacitance	C_{rss}		0.21			
Effective output capacitance, time related ⁴⁾	$C_{o(tr)}$	-	24	-	pF	$V_{GS}=0\text{ V}$; $V_{DS}=0\text{ to }400\text{ V}$; $I_D=\text{const}$
Effective output capacitance, energy related ⁵⁾	$C_{o(er)}$	-	18	-	pF	$V_{DS}=0\text{ to }400\text{ V}$
Output charge	Q_{oss}		9.6	-	nC	
Coss stored energy	E_{oss}		1.4	-	μJ	
Turn-on delay time	$t_{d(on)}$	-	7	-	ns	$I_D=2.1\text{ A}$; $R_{ON}=18\text{ }\Omega$; $R_{OFF}=18\text{ }\Omega$; $R_{SS}=1200\text{ }\Omega$; $C_C=0.82\text{ nF}$; $V_{DRV}=12\text{ V}$; see Table 8
Turn-off delay time	$t_{d(off)}$		9			
Rise time	t_r		6			
Fall time	t_f		28			

⁴⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400 V

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400 V

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate charge	Q_G	-	1.3	-	nC	$V_{GS}=0\text{ to }3\text{ V}$; $V_{DS}=400\text{ V}$; $I_D=2.1\text{ A}$

Table 7 Reverse conduction characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Source-Drain reverse voltage	V_{SD}	-	2.0	2.4	V	$V_{GS}=0\text{ V}; I_{SD}=2.1\text{ A}$
Pulsed current, reverse	$I_{SD,pulse}$	-	-	16	A	$I_G=7.1\text{ mA}$
Reverse recovery charge ⁶⁾	Q_{rr}	-	0	-	nC	$I_{SD}=2.1\text{ A}; V_{DS}=400\text{ V}$

⁶⁾ Excluding Q_{oss}

4 Electrical characteristics diagrams

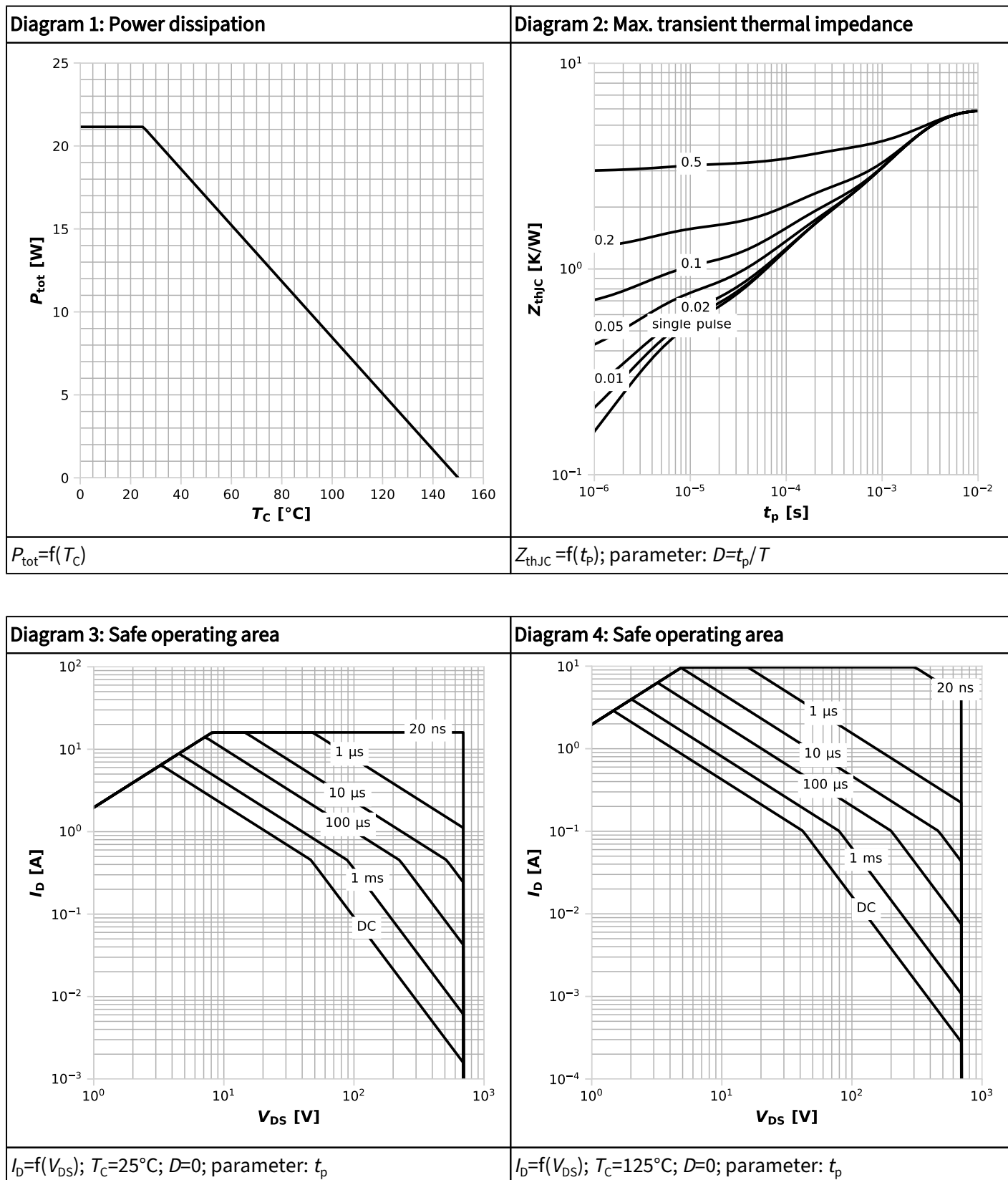
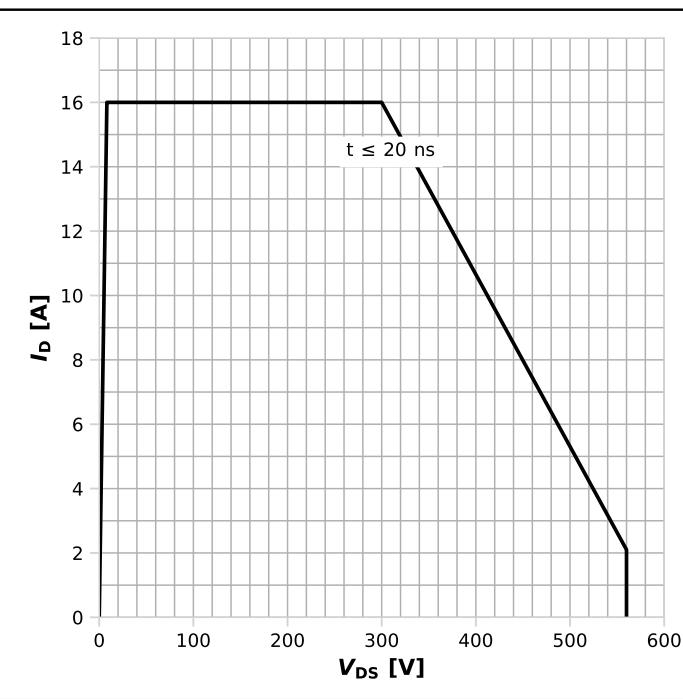
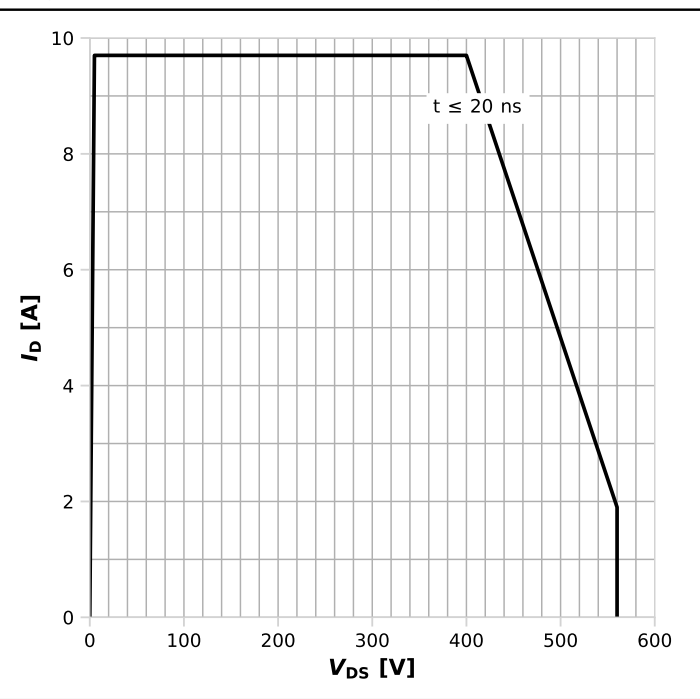


Diagram 5: Repetitive safe operating area



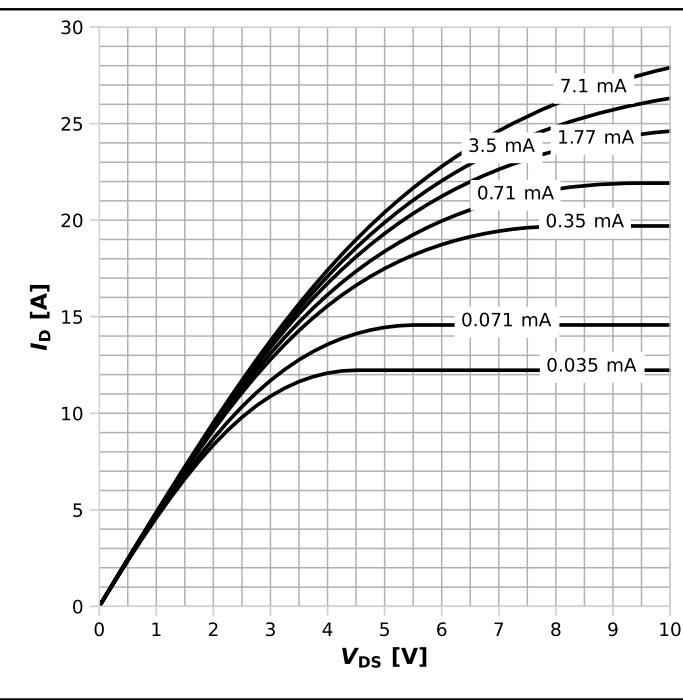
$I_D = f(V_{DS})$; $T_c = 25^\circ\text{C}$; $T_j \leq 150^\circ\text{C}$; parameter: t_p

Diagram 6: Repetitive safe operating area



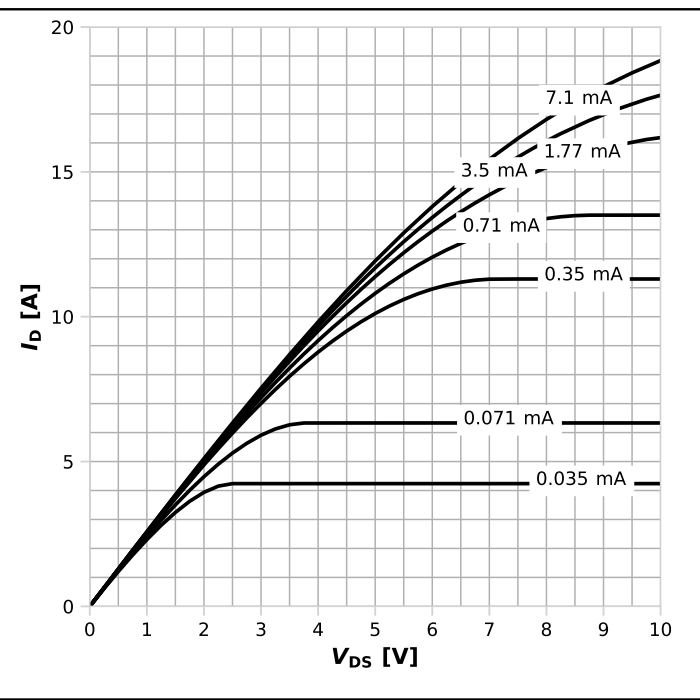
$I_D = f(V_{DS})$; $T_c = 125^\circ\text{C}$; $T_j \leq 150^\circ\text{C}$; parameter: t_p

Diagram 7: Typ. output characteristics



$I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$; parameter: I_{GS}

Diagram 8: Typ. output characteristics



$I_D = f(V_{DS})$; $T_j = 125^\circ\text{C}$; parameter: I_{GS}

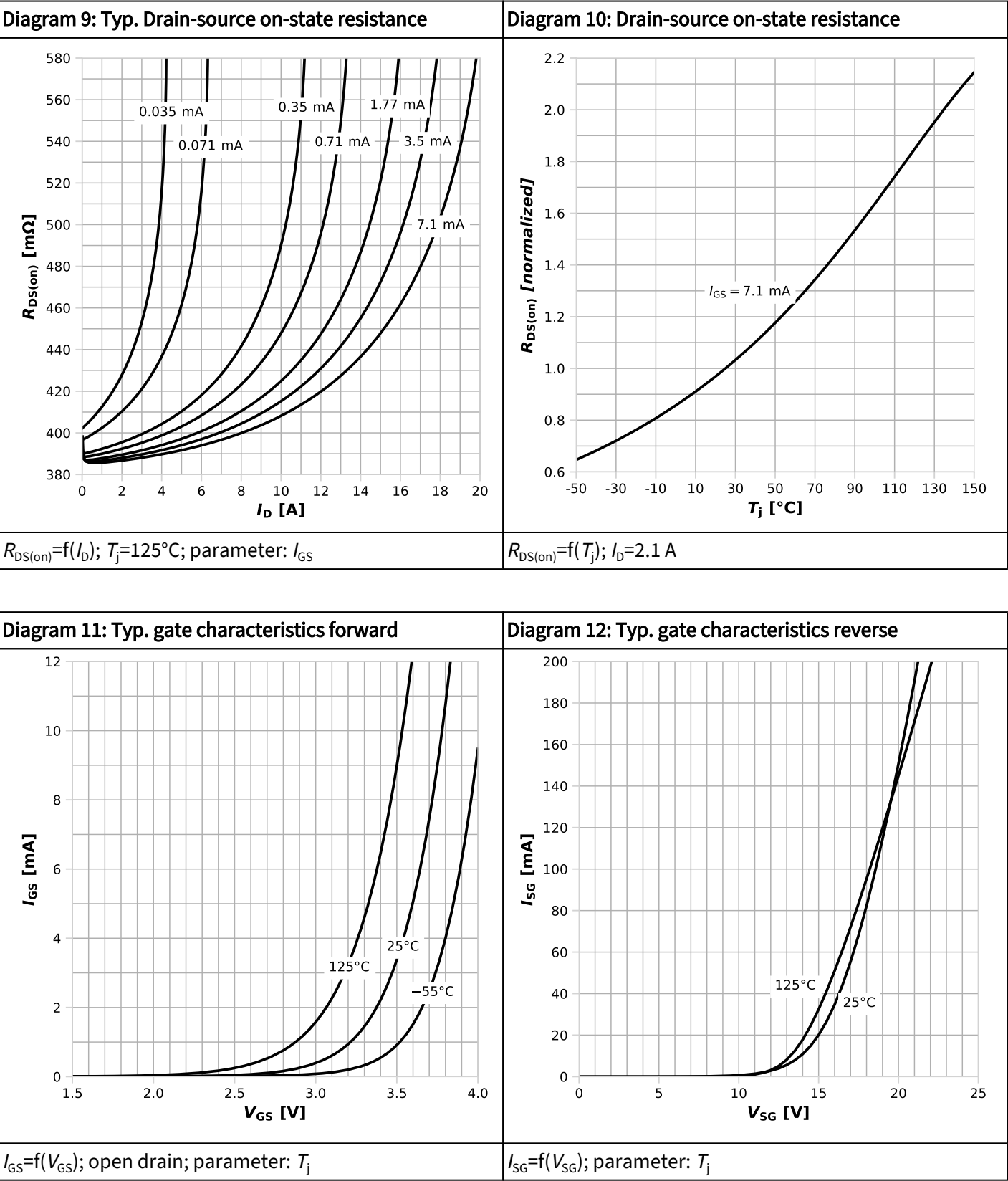
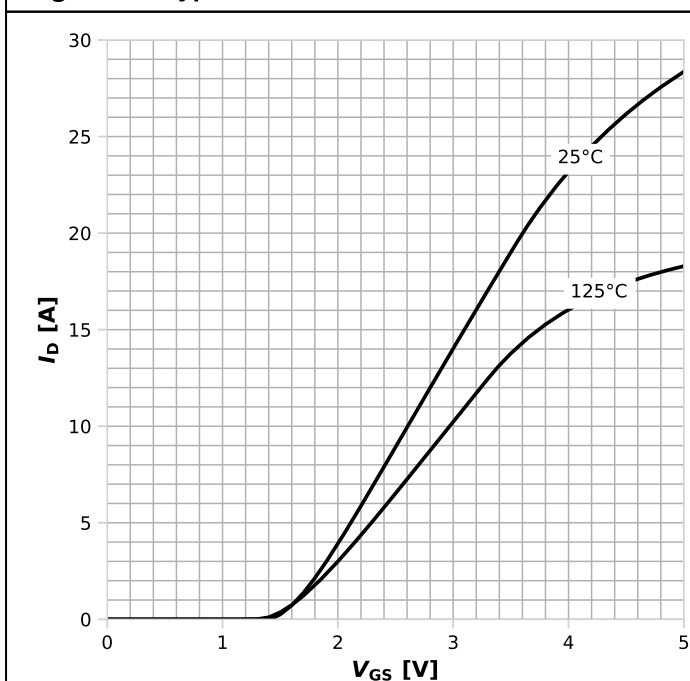
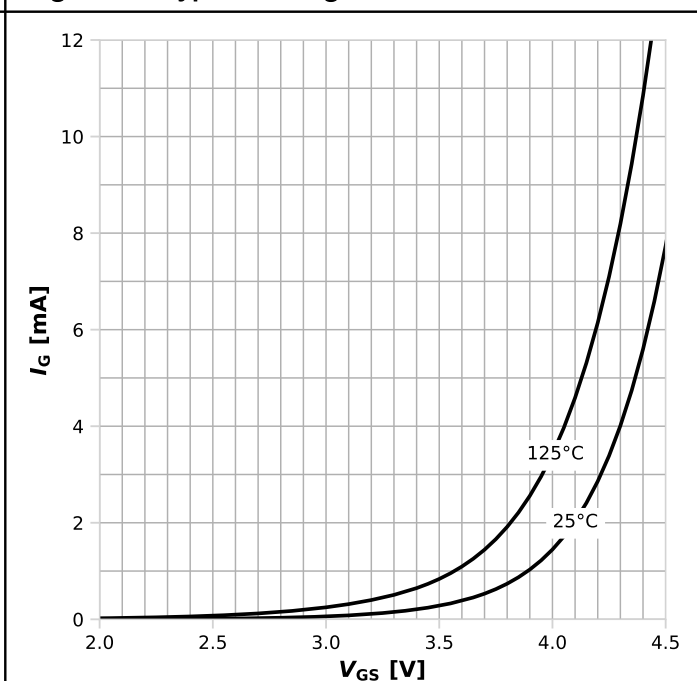


Diagram 13: Typ. transfer characteristics



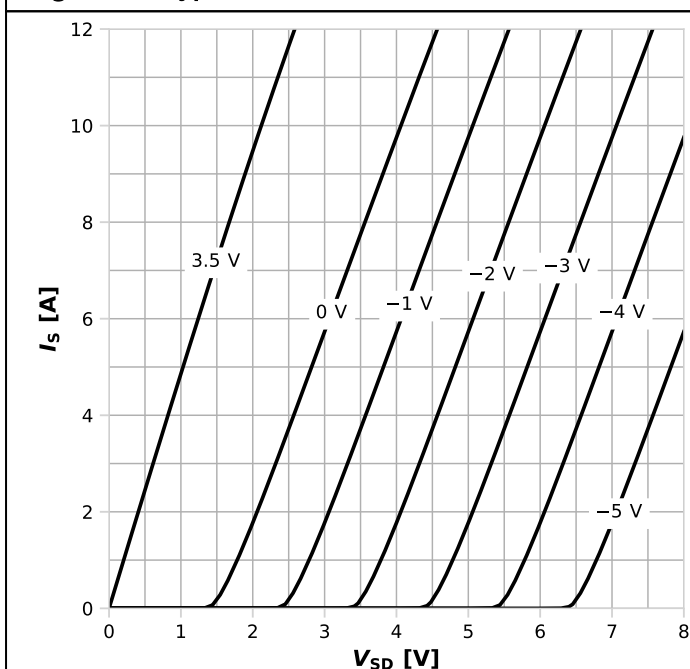
$I_D = f(V_{GS})$; $V_{DS} = 8V$; parameter: T_j

Diagram 14: Typ. transfer gate current characteristic



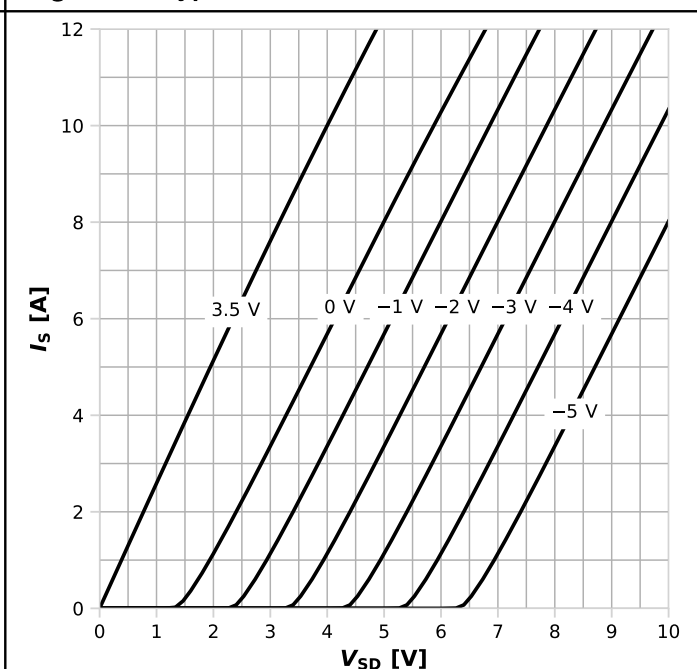
$I_G = f(V_{GS})$; $V_{DS} = 8V$; parameter: T_j

Diagram 15: Typ. channel reverse characteristics



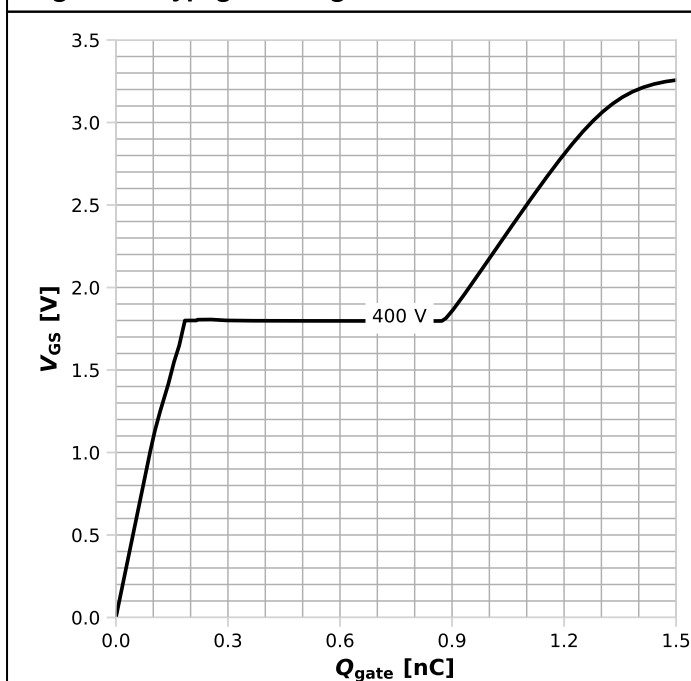
$I_S = f(V_{SD})$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 16: Typ. channel reverse characteristics



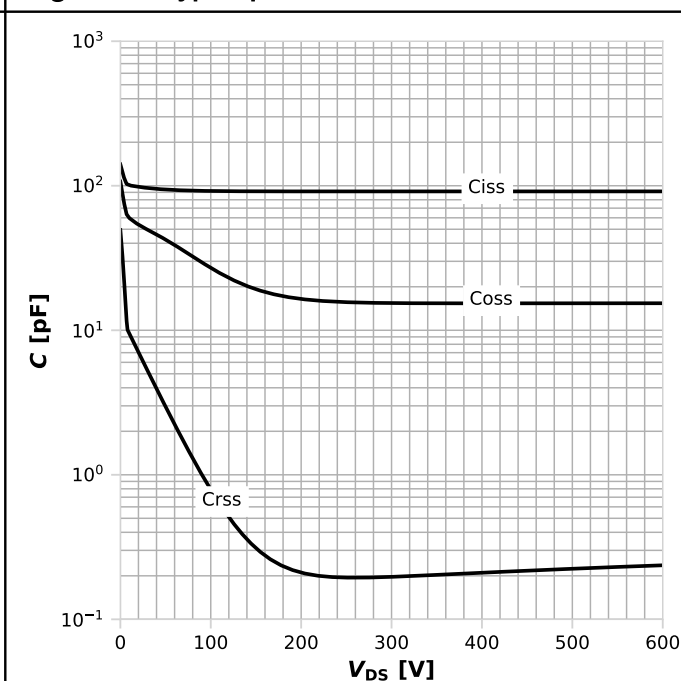
$I_S = f(V_{SD})$; $T_j = 125^\circ\text{C}$; parameter: V_{GS}

Diagram 17 Typ. gate charge



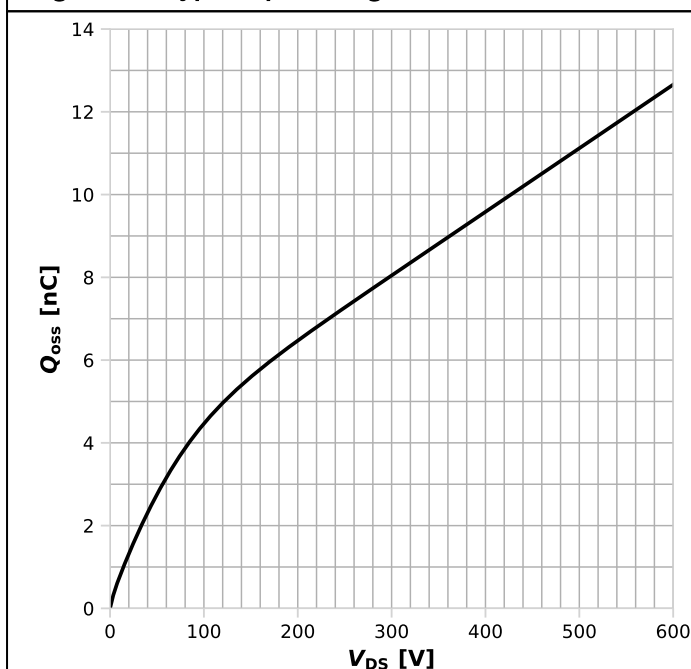
$V_{GS}=f(Q_{gate})$; $I_D=2.1$ A pulsed; $I_G=4.5$ mA; parameter: V_{DD}

Diagram 18: Typ. capacitances



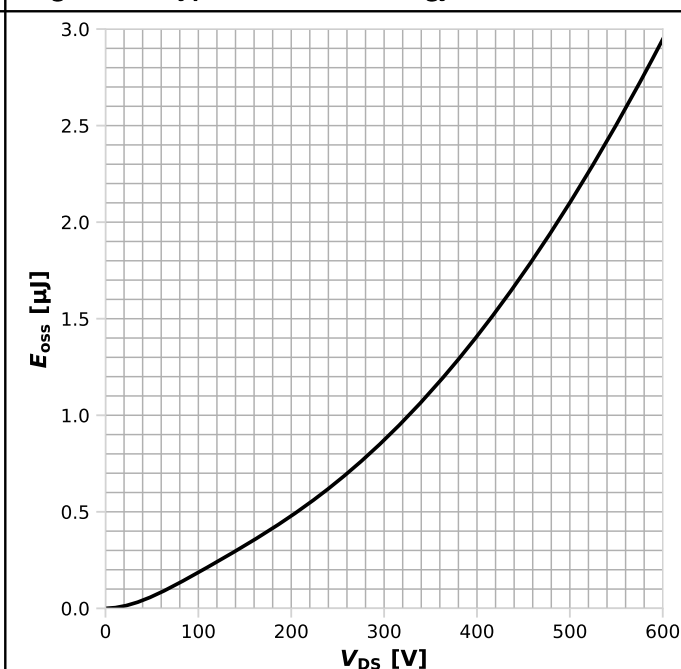
$C=f(V_{DS})$; $V_{GS}=0$ V

Diagram 19: Typ. output charge



$Q_{oss}=f(V_{DS})$

Diagram 20: Typ. Coss stored energy



$E_{oss}=f(V_{DS})$

5 Test circuits

Table 8 Reverse Channel Characteristics Test with Diode

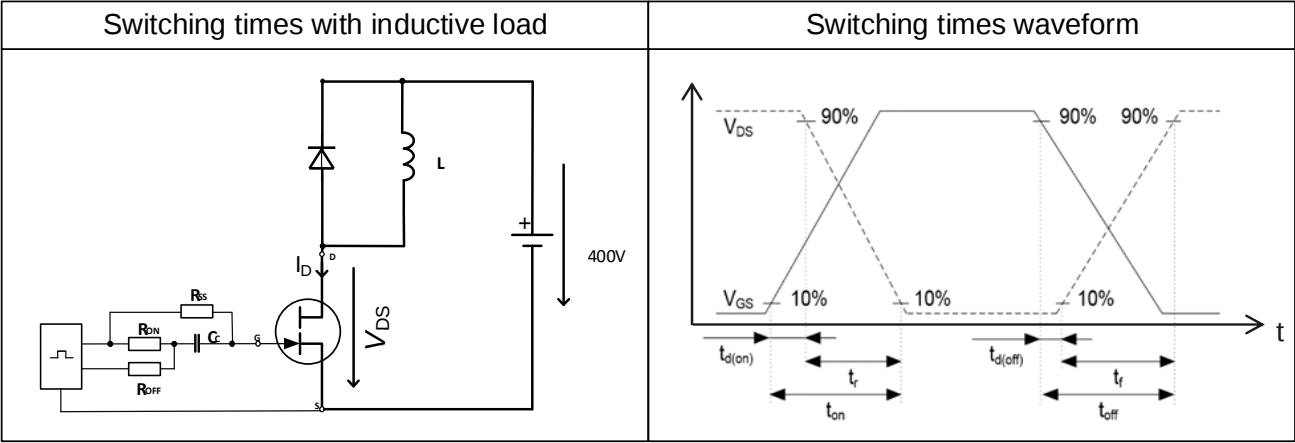
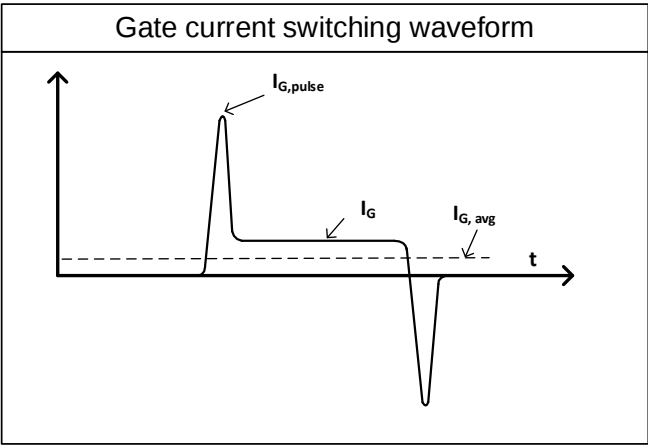
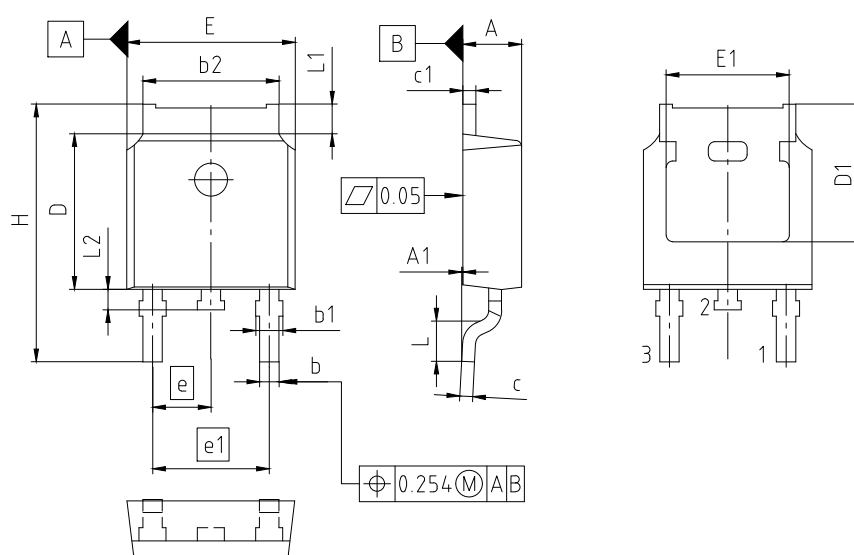


Table 9 Gate current switching waveform



6 Package outlines



PACKAGE - GROUP NUMBER: PG-T0252-3-U03		
REVISION: 01	DATE: 24.11.2021	
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	2.20	2.40
A1	0.00	0.15
b	0.68	0.89
b1	0.72	1.10
b2	5.13	5.50
c	0.46	0.60
c1	0.46	0.60
D	5.98	6.22
D1	5.25	5.40
E	6.40	6.73
E1	4.70	5.60
e	2.29	
e1	4.57	
N	3	
H	9.40	10.48
L	1.38	1.70
L1	0.90	1.25
L2	0.60	1.00

ALL DIMENSIONS REFER TO JEDEC
STANDARD TO-252 AND DO NOT INCLUDE MOLD
FLASH OR PROTRUSIONS.

Figure 1 Outline PG-T0252-3, dimensions in mm

7 Appendix A

Table 10 **Related links**

- CoolGaN™ webpage
- CoolGaN™ reliability white paper
- CoolGaN™ gate driver application note
- CoolGaN™ applications information

Revision history

IGD70R200D2S

Revision 2025-05-30, Rev. 1.3

Previous revisions

Revision	Date	Subjects (major changes since last revision)
1.0	2025-04-14	Release of final version
1.1	2025-04-23	Package information update
1.2	2025-05-16	2kV ESD robustness
1.3	2025-05-30	Potential application update

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